# S3AB - S3MB

Taiwan Semiconductor

# 3A, 50V - 1000V Surface Mount Rectifier

### FEATURES

TAIWAN

Glass passivated chip junction

SEMICONDUCTOR

- Ideal for automated placement
- Low forward voltage drop
- High surge current capability
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

## APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- Lighting application
- Converter

## **MECHANICAL DATA**

- Case: DO-214AA (SMB)
- Molding compound meets UL 94V-0 flammability rating
- Part no. with suffix "H" means AEC-Q101 qualified
- Packing code with suffix "G" means green compound (halogen-free)
- Moisture sensitivity level: level 1, per J-STD-020
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 0.09 g (approximately)

KEY PARAMETERS					
PARAMETER	VALUE	UNIT			
I <sub>F(AV)</sub>	3	А			
V <sub>RRM</sub>	50 - 1000	V			
I <sub>FSM</sub>	80	А			
T <sub>J MAX</sub>	150 °C				
Package	DO-214AA (SMB)				
Configuration	Single Die				





DO-214AA (SMB)

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)									
PARAMETER	SYMBOL	S3AB	S3BB	S3DB	S3GB	S3JB	S3KB	S3MB	UNIT
Marking code on the device		S3AB	S3BB	S3DB	S3GB	S3JB	S3KB	S3MB	
Repetitive peak reverse voltage	V <sub>RRM</sub>	50	100	200	400	600	800	1000	V
Reverse voltage, total rms value	V <sub>R(RMS)</sub>	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V <sub>DC</sub>	50	100	200	400	600	800	1000	V
Forward current	I <sub>F(AV)</sub>				3				Α
Surge peak forward current, 8.3 ms single half sine-wave superimposed on rated load per diode	I <sub>FSM</sub>	80			A				
Junction temperature	TJ	J - 55 to +150			°C				
Storage temperature	T <sub>STG</sub>	T <sub>STG</sub> - 55 to +150			°C				



THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-lead thermal resistance	$R_{\Theta JL}$	10	°C/W

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_A = 25^{\circ}C$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	ТҮР	MAX	UNIT	
Forward voltage per diode <sup>(1)</sup>	$I_F = 3A, T_J = 25^{\circ}C$	V <sub>F</sub>	-	1.15	V	
	$T_J = 25^{\circ}C$		-	10	μA	
Reverse current @ rated $V_R$ per diode <sup>(2)</sup>	T <sub>J</sub> = 125°C	I <sub>R</sub>	-	250	μA	
Junction capacitance	1 MHz, V <sub>R</sub> =4.0V	CJ	40	-	pF	
Reverse recovery time	I <sub>F</sub> =0.5A , I <sub>R</sub> =1.0A I <sub>RR</sub> =0.25A	+	1500	-	20	
Reverse recovery line	I <sub>RR</sub> =0.25A	t <sub>rr</sub>			ns	

#### Notes:

1. Pulse test with PW=0.3 ms

2. Pulse test with PW=30 ms

ORDERING INFORMATION							
PART NO.	PART NO. SUFFIX	PACKING CODE	PACKING CODE SUFFIX(*)	PACKAGE	PACKING		
	н	R5	R5		850 / 7" Plastic reel		
S3xB		R4	G	SMB	3,000 / 13" Paper reel		
(Note 1)		M4		SMB	3,000 / 13" Plastic reel		

Note:

1. "x" defines voltage from 50V (S3AB) to 1000V (S3MB)

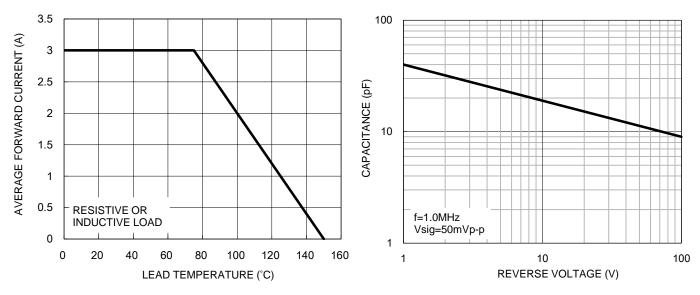
\*: Optional available

EXAMPLE P/N					
EXAMPLE P/N	PART NO.	PART NO. SUFFIX	PACKING Code	PACKING CODE SUFFIX	DESCRIPTION
S3ABHR5G	S3AB	Н	R5	G	AEC-Q101 qualified Green compound

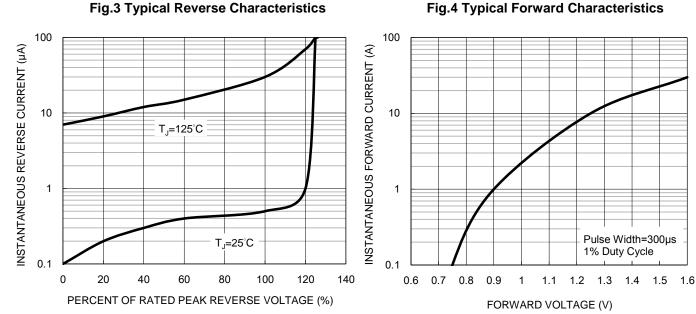


## **CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25°C unless otherwise noted)



#### Fig.1 Forward Current Derating Curve

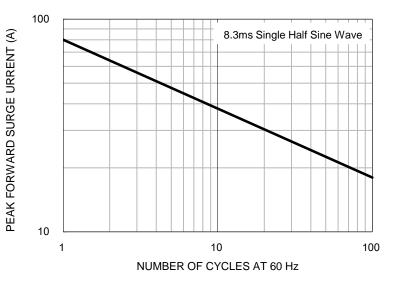


ent Derating Curve

#### Fig.2 Typical Junction Capacitance

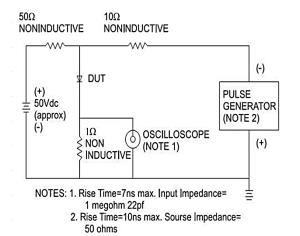


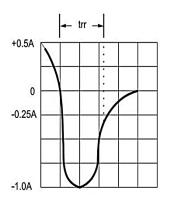
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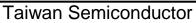


#### Fig.5 Maximum Non-repetitive Forward Surge Current

#### Fig.6 Reverse Recovery Time Characteristic And Test Circuit Diagram



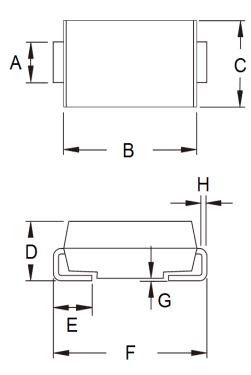






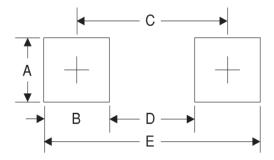
## **PACKAGE OUTLINE DIMENSIONS**

DO-214AA (SMB)



DIM.	Unit (mm)		Unit (inch)		
Dilvi.	Min	Max	Min	Max	
А	1.95	2.20	0.077	0.087	
В	4.05	4.60	0.159	0.181	
С	3.30	3.95	0.130	0.156	
D	1.95	2.65	0.077	0.104	
Е	0.75	1.60	0.030	0.063	
F	5.10	5.60	0.201	0.220	
G	0.05	0.20	0.002	0.008	
Н	0.15	0.31	0.006	0.012	

## SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
А	2.3	0.091
В	2.5	0.098
С	4.3	0.169
D	1.8	0.071
E	6.8	0.268

## **MARKING DIAGRAM**



P/N

= Marking Code = Green Compound G

YW = Date Code

F = Factory Code



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